JCT151C-800R 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151C-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.

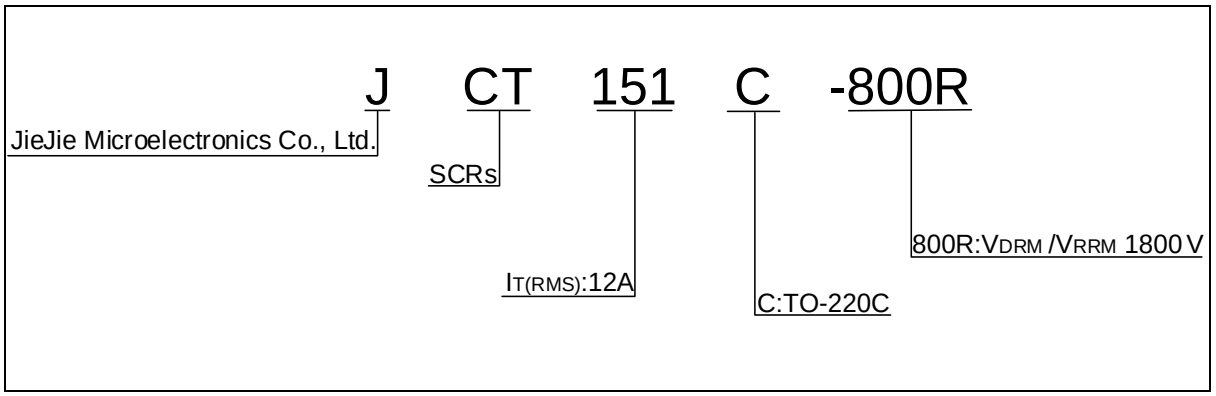
It i> tc08 Tw 2.78 0 Td ( )Tj 0.004 2c -0.004 [illegible]

Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage

(T jvTJ ET Q D q e W (e)]TJ ET Q q 9410

ORDERING INFORMATION



MARKING

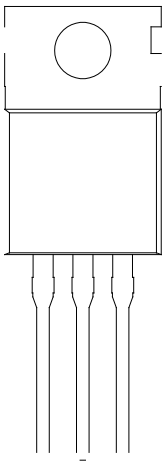


FIG.1: Maximum power dissipation versus RMS on-state current

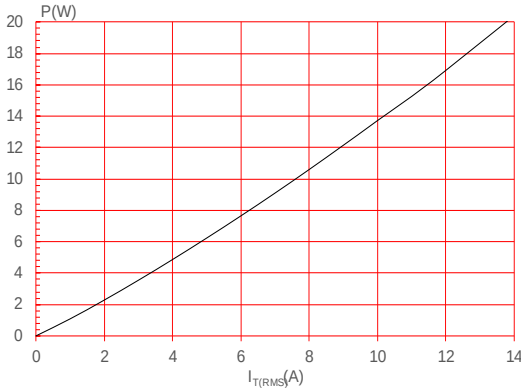


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



PACKAGE MECHANICAL DATA

